



Семинар

**Среда, 8 февраля,
11-00**

Конференц-зал ЛЯП

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" Radiation hardness of GaAs:Cr and Si sensors irradiated by 20 MeV electron beam "

The interest in using of sensors from high resistivity gallium arsenide compensated by chromium (GaAs:Cr) for nuclear and high energy physics has been growing steadily due to its numerous advantages over silicon. At the same time, the radiation hardness of GaAs:Cr sensors is much less studied. Several test beams were performed at the JINR LINAC-800 accelerator where GaAs:Cr sensors were irradiated by 20 MeV electron beam in direct comparison with Si sensors. Absorbed dose reached the values up to 1.5 MGy. We present the results of radiation hardness measurements that include investigation of I-V characteristics charge collection efficiency and it dependence on the bias voltage for different doses.

(в связи с перевыборами на должность снс)